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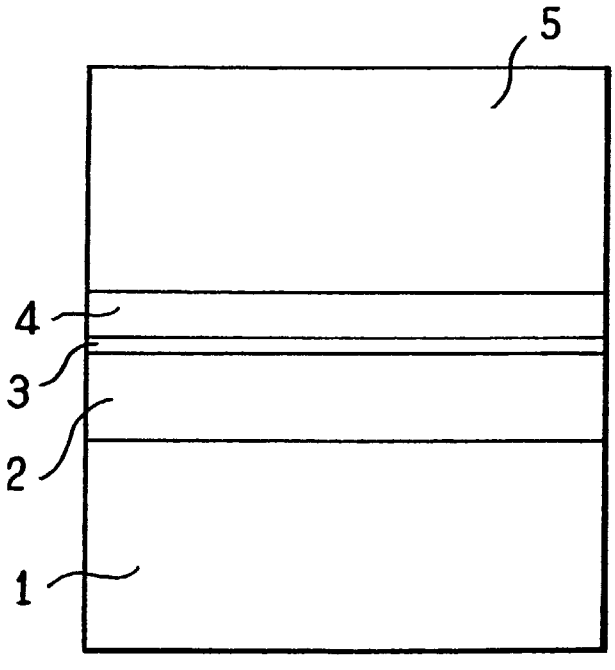
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(54) Title: TRANSFER OF A THIN LAYER FROM A WAFER COMPRISING A BUFFER LAYER



(57) Abstract: Method of producing a structure comprising a thin layer of semiconductor material obtained from a wafer (10), the wafer (10) comprising a lattice parameter matching layer (2) comprising an upper layer of semiconductor material having a first lattice parameter, a film (3) of semiconductor material which has a nominal lattice parameter substantially different from the first lattice parameter and is strained by the matching layer (2), a relaxed layer (4) having a nominal lattice parameter substantially identical to the first lattice parameter, the metod comprising transfer of the relaxed layer (4) and the strained film (3) to a receiving substrate (5). Structures produced according to one of the processes according to the invention.

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